

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary.)</i>			Docket Number (Optional) BUR920020068US1		Application Number 10/539,247		
			Applicant(s) Anne Gattiker et al.				
			Filing Date June 16, 2005		Group Art Unit 2820		
			U.S. PATENT DOCUMENTS				
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
VN		Ali Keshavarzi et al., "Intrinsic Leakage in Low Power Deep Submicron CMOS ICs", International Test Conference 1997 (IEEE Cat. No. 97CH36126), pp. 146-155.					
EXAMINER /Vinh Nguyen/			DATE CONSIDERED		01/17/2007		
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